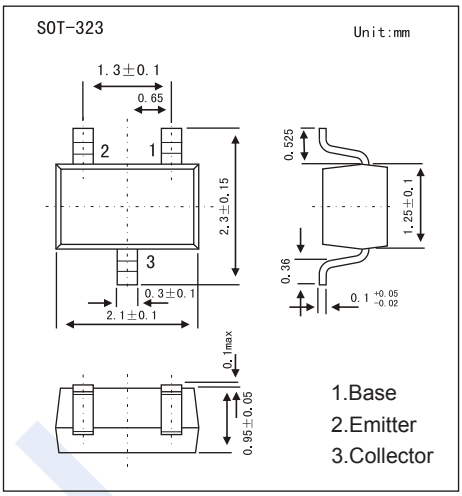
PNP Transistors

MMSTA56 (KMSTA56)



■ Features

- Small Surface Mount Package
- General Poupose for Amplification

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-80	V
Collector - Emitter Voltage	V_{CEO}	-80	
Emitter - Base Voltage	V_{EBO}	-4	
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\Theta JA}$	625	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E= 0	-80			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B= 0	-80			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C= 0	-4			
Collector-base cut-off current	I_{CBO}	V_{CB}= -80 V , I_E= 0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100 mA, I_B=-10mA			-0.25	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-100 mA, I_B=-10mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}= -1V, I_C= -100mA			-1.2	
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -10mA	50			
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -100mA	50			
Transition frequency	f_T	V_{CE}= -1V, I_C= -100mA,f=100MHz	50			MHz

■ Marking

Marking	K2G